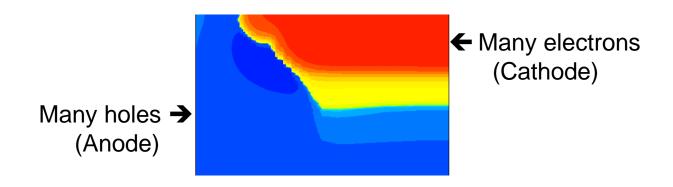
# Lecture4: Diode (2)

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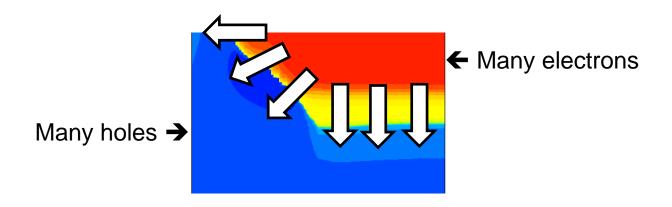
### Equilibrium (1)

- When the applied voltage is zero, no current occurs.
  - Many electrons in the "red" region. (Doped with Arsenic ions. "ntype")
  - Many holes in the "blue" region. (Doped with Boron ions. "p-type")
  - Due to the diffusion mechanism, they tend to spread over.
  - Then, we will have the net current! (It's not possible.)



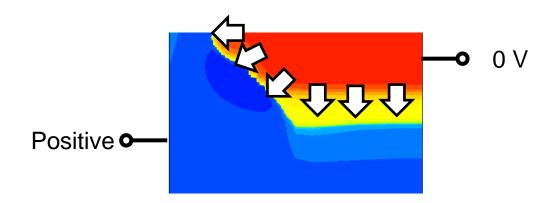
# Equilibrium (2)

- An electric field is built. (Built-in field)
  - It pushes the electrons back to the n-type region.
  - It pushes the holes back to the p-type region.
  - Direction of the electric field?
  - At equilibrium, drift (due to the electric field) and diffusion (due to the density difference) are exactly matched.



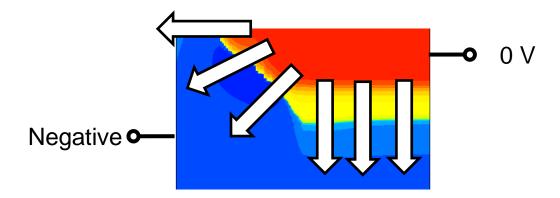
#### **Forward bias**

- We have a positive voltage at the anode.
  - Additional electric field from positive to 0 V
  - The external voltage opposes the built-in potential.
  - No sufficiently strong electric field to prevent the diffusion
  - It raises the diffusion currents substantially.



#### Reverse bias

- We have a negative voltage at the anode.
  - Additional electric field from 0 V to negative
  - The applied voltage enhances the field.
  - Even stronger electric field to prevent the diffusion
  - It prohibits the current flow.
- Highly nonlinear operation!



### IV characteristics (1)

#### Review

- The diode current,  $I_D$ , is depedent on the diode voltage,  $V_D$ .
- Then, what is  $I_D(V_D)$ ?
- Compare  $V_D = 0.3 \text{ V}$ , 0.4 V, and 0.5 V.
  - We know that the electric field for 0.5 V is weakest.
  - Of course, for 0.3 V, it is strongest.
  - Anyway, they are different by a constant voltage, 0.1 V.
  - Then, what about  $I_D(0.3)$ ,  $I_D(0.4)$ , and  $I_D(0.5)$ ?
  - Do you expect a linear dependence?

# IV characteristics (2)

- Exponential dependence on  $V_D$ 
  - $V_D$  is normalized by the thermal voltage,  $V_T = \frac{k_B T}{q}$ .
  - At 300 K,  $V_T$  ≈ 0.002585 V = 25.85 mV.
  - Then, the diode current can be written as

$$I_D = I_S \left( \exp \frac{V_D}{V_T} - 1 \right)$$

– Here, the "reverse saturation current" ( $I_S$ ) is a given constant. It's a small current.

# IV characteristics (3)

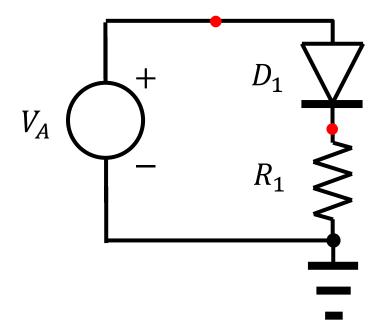
Some limiting cases:

$$I_D = I_S \left( \exp \frac{V_D}{V_T} - 1 \right)$$

- When  $V_D$  is close to zero,  $\exp \frac{V_D}{V_T} \approx 1 + \frac{V_D}{V_T}$   $I_D = I_S \frac{V_D}{V_T}$
- When  $V_D$  is negative and  $V_D \ll -V_T$ ,  $\exp \frac{V_D}{V_T} \approx 0$   $I_D = -I_S$
- When  $V_D$  is positive and  $V_D \gg V_T$ ,  $I_D = I_S \exp \frac{V_D}{V_T}$

#### **General solution (1)**

- Analyze the following circuit. (A diode-resistor combination)
  - Calculation of node voltages and terminal currents



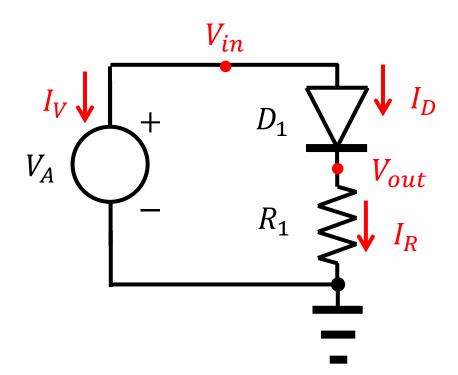
# **General solution (2)**

- Identify the nodes and apply the KCL.
  - Two nodes (red dots) are found.

$$I_V + I_D = 0$$
  
$$-I_D + I_R = 0$$

Equations for terminal IVs

$$\begin{aligned} V_{in} &= V_A \\ I_D &= I_S \left( \exp \left( \frac{V_{in} - V_{out}}{V_T} \right) - 1 \right) \\ I_R &= \frac{V_{out}}{R_1} \end{aligned}$$



# **General solution (3)**

- Solve the set of equations.
  - After simple manipulation, it is easily found that

$$-I_S\left(\exp\left(\frac{V_A - V_{out}}{V_T}\right) - 1\right) + \frac{V_{out}}{R_1} = 0$$

- An nonlinear equation for  $V_{out}$  is obtained.
- The solution,  $V_{out}$ , can be visualized by drawing the following two curves.

$$y = I_S \left( \exp\left(\frac{V_A - x}{V_T}\right) - 1 \right)$$
$$y = \frac{x}{R_1}$$

### **Graphical solution (1)**

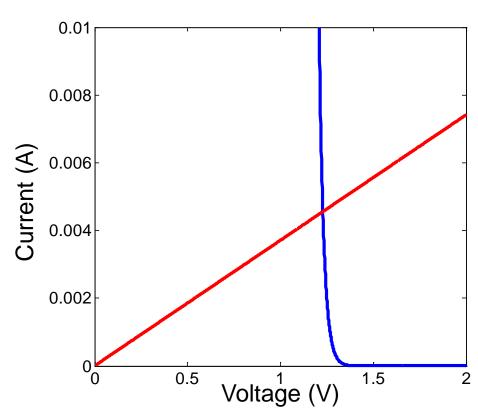
- Assume that  $V_A = 2 \text{ V}$ ,  $I_S = 0.5 \text{ fA}$ , and  $R_1 = 270 \Omega$ .
  - Draw two curves:

$$y = I_S \left( \exp\left(\frac{V_A - x}{V_T}\right) - 1 \right)$$
$$y = \frac{x}{R_1}$$

The answer is

$$V_{out} = 1.2287 \text{ V}.$$

0.77 V is applied to the diode.

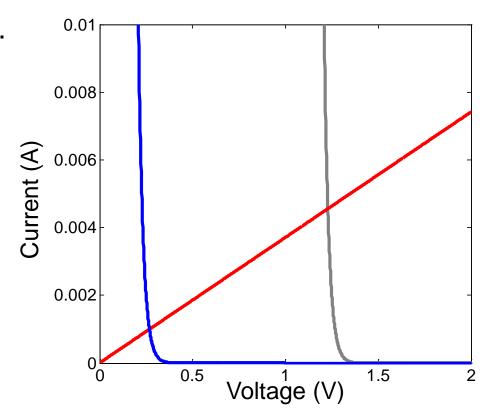


### **Graphical solution (2)**

- Reduce  $V_A$  to 1 V.
  - The answer is

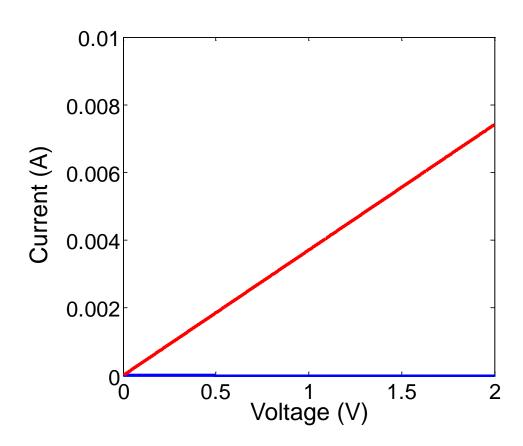
 $V_{out} = 0.2687 \text{ V}.$ 

- 0.73 V is applied to the diode.
- Even smaller V<sub>A</sub>?
  - For example, 0.5 V?



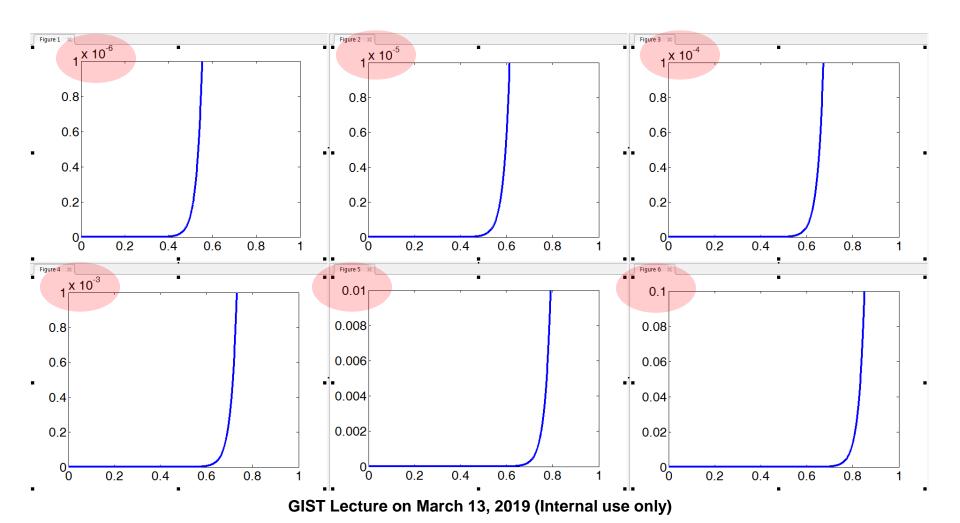
#### When $V_A = 0.5 \text{ V}$

- The same scale as before.
  - ???
  - What is  $V_{out}$ ?
- Not enough V<sub>A</sub>
  - No current conduction



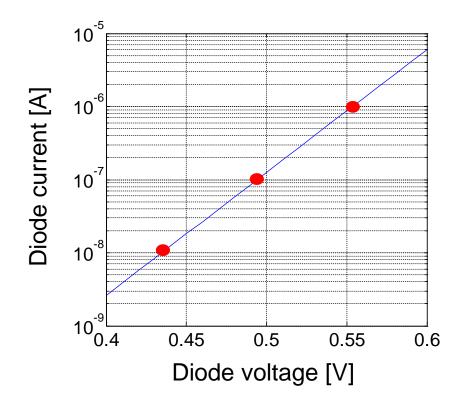
#### **Dioide IV curves**

• A diode with  $I_S = 5 \times 10^{-16} \text{A}$  (Only different y scales)



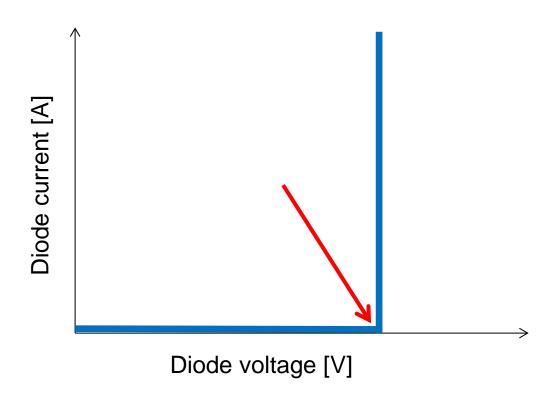
#### Important observation

- In order to obtain 10x large current,
  - We must apply only 60 mV additionally. (300K)



#### **Diode model**

Two phases



#### Homework#2

- Due: 09:00, March 18
  - Submit your Homework answer sheet (hardcopy) directly to Mr.
     Suhyeong Cha, our TA.
  - His office: EECS building C-411
- Solve following problems of the 2018 mid-term exam.
  - P8
  - P9
  - P11
- Solve following problems of the 2017 mid-term exam.
  - P10
  - P11
  - P14
  - P17